
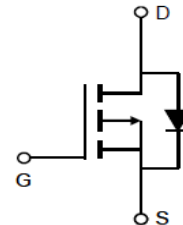
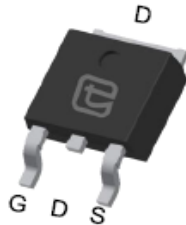


**30V P-Channel Trench MOSFET(Preliminary)**

<p>General Description</p> <ul style="list-style-type: none"> ● Trench Power technology ● Low $R_{DS(ON)}$ ● Low Gate Charge ● Optimized for fast-switching applications <p>Applications</p> <ul style="list-style-type: none"> ● Synchronous Rectification in DC/DC and AC/DC Converters ● Isolated DC/DC Converters in Telecom and Industrial 	<p>Product Summary</p> <table> <tr> <td>V_{DS}</td> <td>-30V</td> </tr> <tr> <td>I_D (at $V_{GS}=10V$)</td> <td>-110A</td> </tr> <tr> <td>$R_{DS(ON)}$ (at $V_{GS}=-10V$)</td> <td>< 6.5mΩ</td> </tr> <tr> <td>$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)</td> <td>< 10mΩ</td> </tr> </table> <p>100% UIS Tested</p> 	V_{DS}	-30V	I_D (at $V_{GS}=10V$)	-110A	$R_{DS(ON)}$ (at $V_{GS}=-10V$)	< 6.5m Ω	$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	< 10m Ω
V_{DS}	-30V								
I_D (at $V_{GS}=10V$)	-110A								
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	< 6.5m Ω								
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	< 10m Ω								

TO-252



Part Number	Package Type	Form	Marking
TTD110P03AT	TO-252	Tape&Reel	110P03AT

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	- 30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^B	I_D	$T_C = 25^\circ\text{C}$	-46
		$T_C = 100^\circ\text{C}$	-46
Pulsed Drain Current ^A	I_{DM}	-330	A
Avalanche Current ^A	I_{AS}	-30	A
Single Pulse Avalanche Energy $L = 0.3\text{mH}$ ^A	E_{AS}	135	mJ
Power Dissipation ^C	P_D	$T_C = 25^\circ\text{C}$	83
		$T_C = 100^\circ\text{C}$	42
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case	Steady-State $R_{\theta JC}$	1.8	$^\circ\text{C/W}$
Maximum Junction-to-Ambient	Steady-State $R_{\theta JA}$	100	



Electrical Characteristics($T_J = 25^\circ\text{C}$ unless otherwise noted)						
Symbol	Parameter	Conditions	Value			Units
			Min	Typ	Max	
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$	$T_J = 25^\circ\text{C}$		-1	μA
			$T_J = 100^\circ\text{C}$		-100	
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1	-1.7	-2.4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{V}, I_D = -20\text{A}$		5.3	6.5	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}, I_D = -20\text{A}$		9	10	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{V}, I_D = -20\text{A}$		31		S
V_{SD}	Diode Forward Voltage	$I_S = -20\text{A}, V_{GS} = 0\text{V}$			-1	V
I_S	Maximum Body-Diode Continuous Current ^B				-46	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = -15\text{V}, f = 1\text{MHz}$		6182		pF
C_{oss}	Output Capacitance			571		
C_{rss}	Reverse Transfer Capacitance			555		
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS} = -10\text{V}, V_{DS} = -15\text{V}, I_D = -20\text{A}$		100		nC
Q_{gs}	Gate Source Charge			18		
Q_{gd}	Gate Drain Charge			32		
$t_{D(on)}$	Turn-On Delay Time	$V_{GS} = -10\text{V}, V_{DS} = -15\text{V}, I_D = -20\text{A}, R_G = 2.5\Omega$		212		ns
t_r	Turn-On Rise Time			290		
$T_{D(off)}$	Turn-Off Delay Time			15		
t_f	Turn-Off Fall Time			11		
t_{rr}	Body Diode Reverse Recovery Time	$I_F = -15\text{A}, di/dt = 100\text{A}/\mu\text{s}$		34		ns
Q_{rr}	Body Diode Reverse Recovery Charge			79		nC

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation P_D is based on $T_{J(MAX)} = 175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

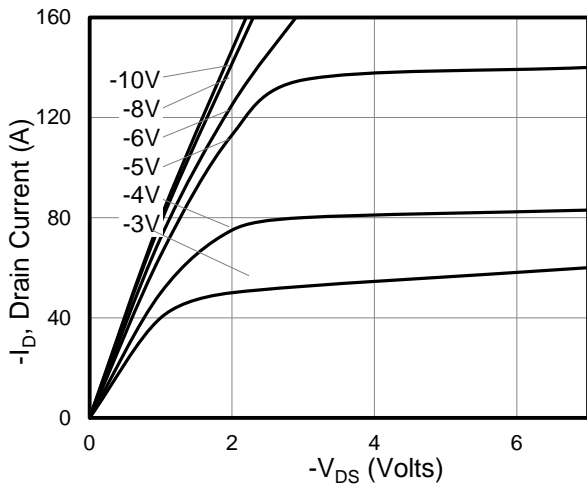


Figure 1: On-Region Characteristics

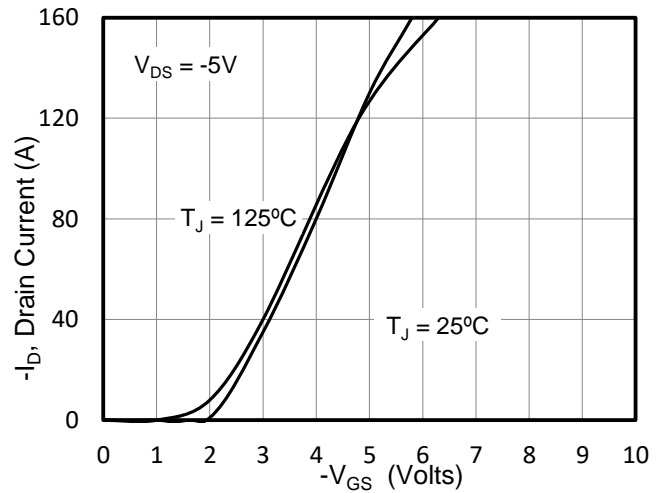


Figure 2: Transfer Characteristics

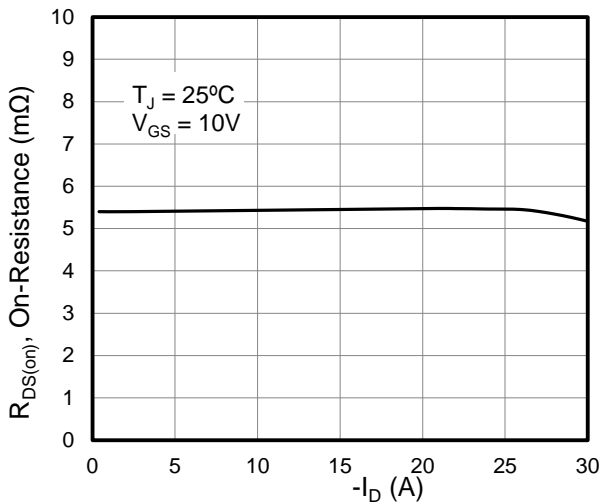


Figure 3: On-Resistance vs. Drain Current

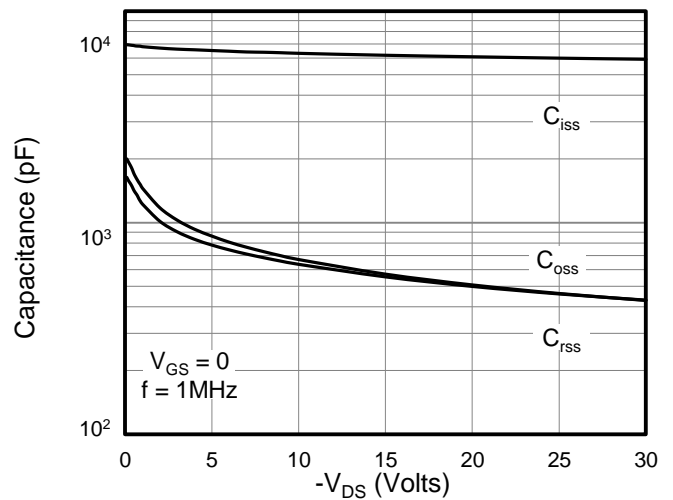


Figure 4: Capacitance Characteristics

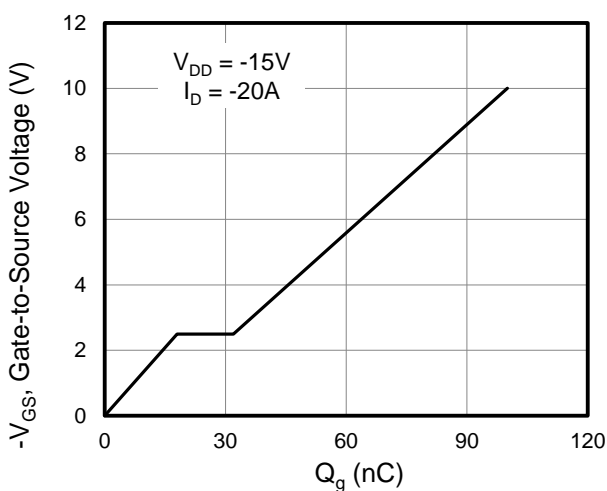


Figure 5: Gate Charge Characteristics

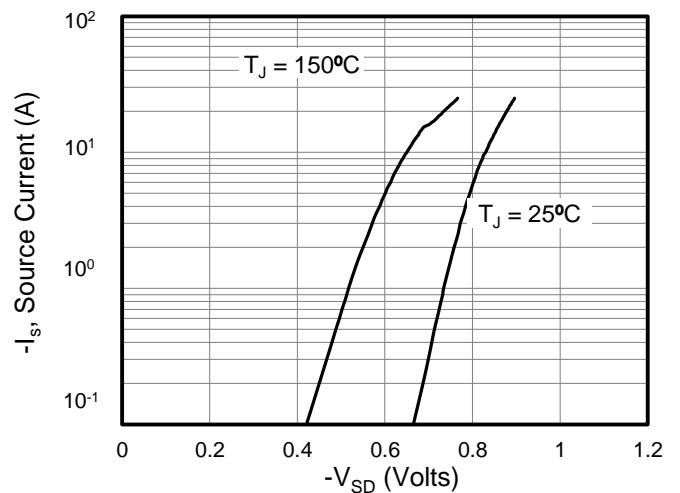


Figure 6: Body Diode Forward Voltage



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

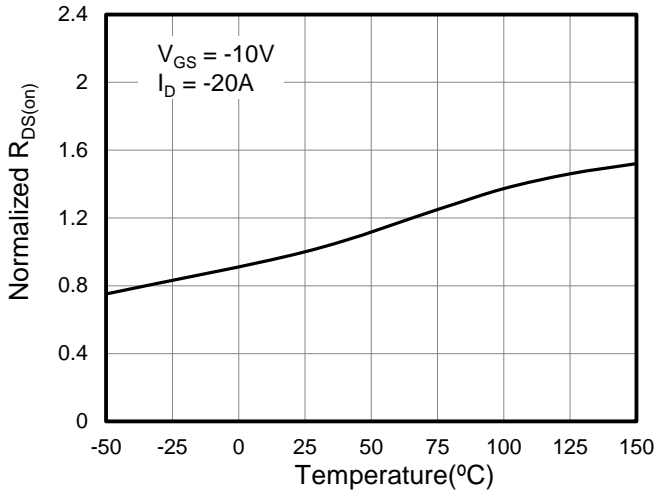


Figure 7: On-Resistance vs. Junction Temperature

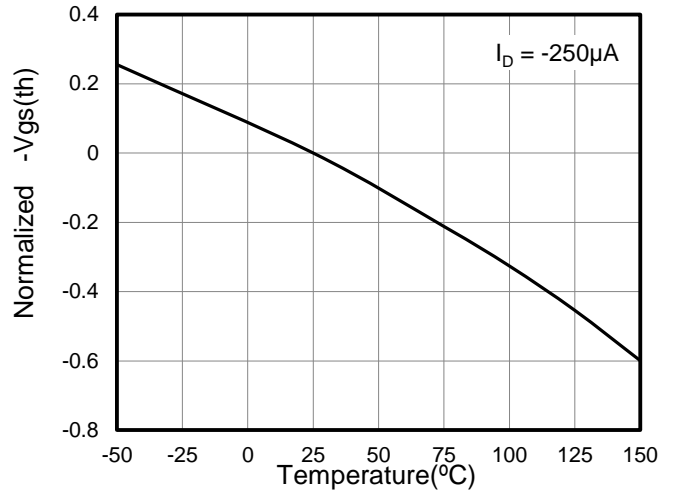


Figure 8: $V_{GS(th)}$ vs. Junction Temperature

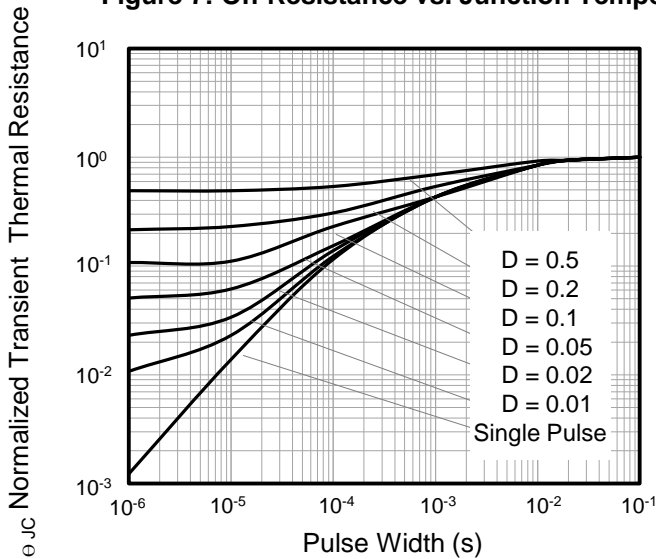


Figure 11: Normalized Transient Thermal Resistance

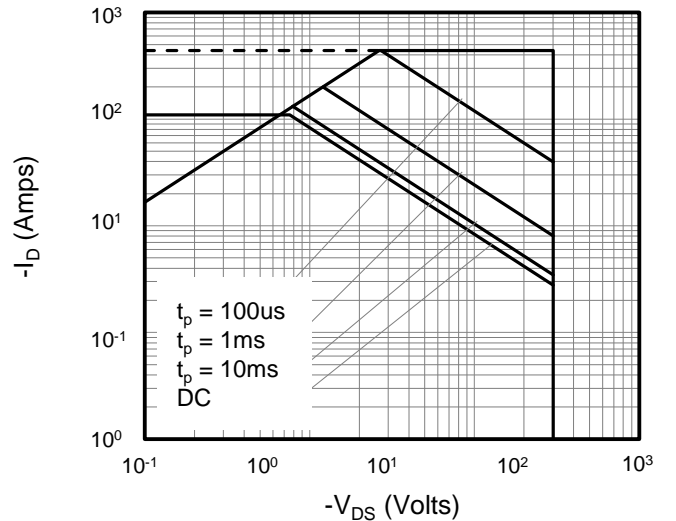


Figure 12: Safe Operating Area



Figure A: Gate Charge Test Circuit and Waveform

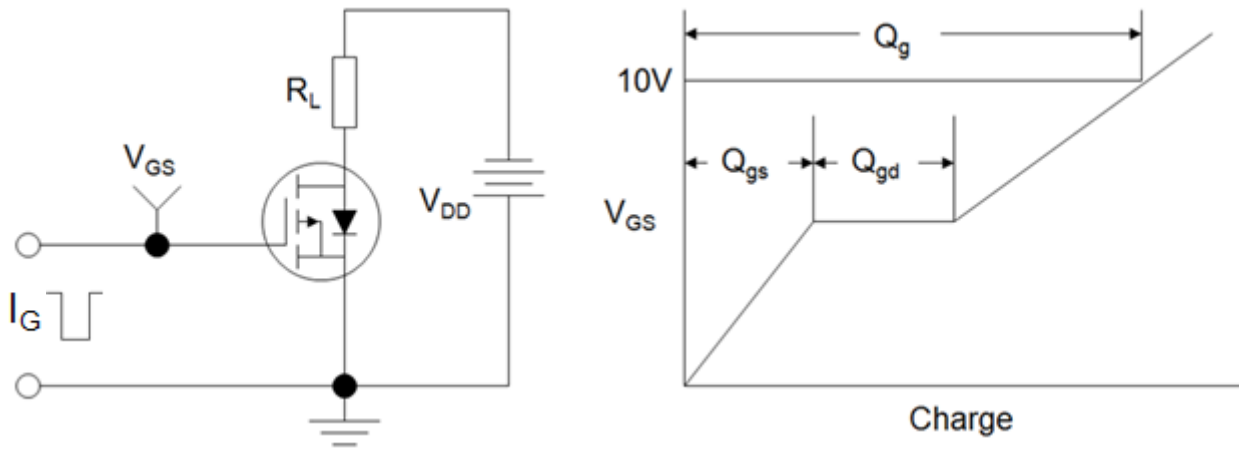


Figure B: Resistive Switching Test Circuit and Waveform

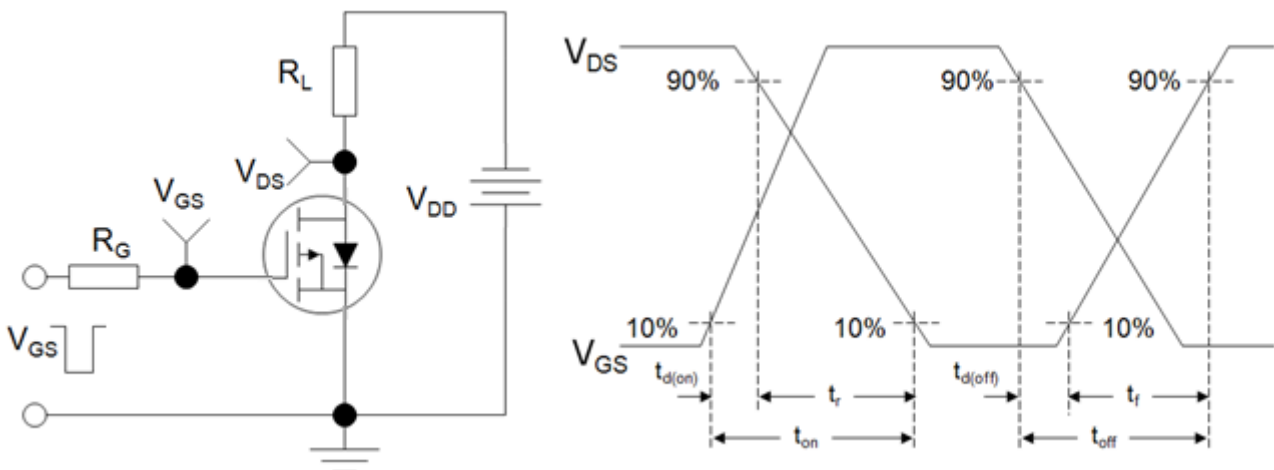
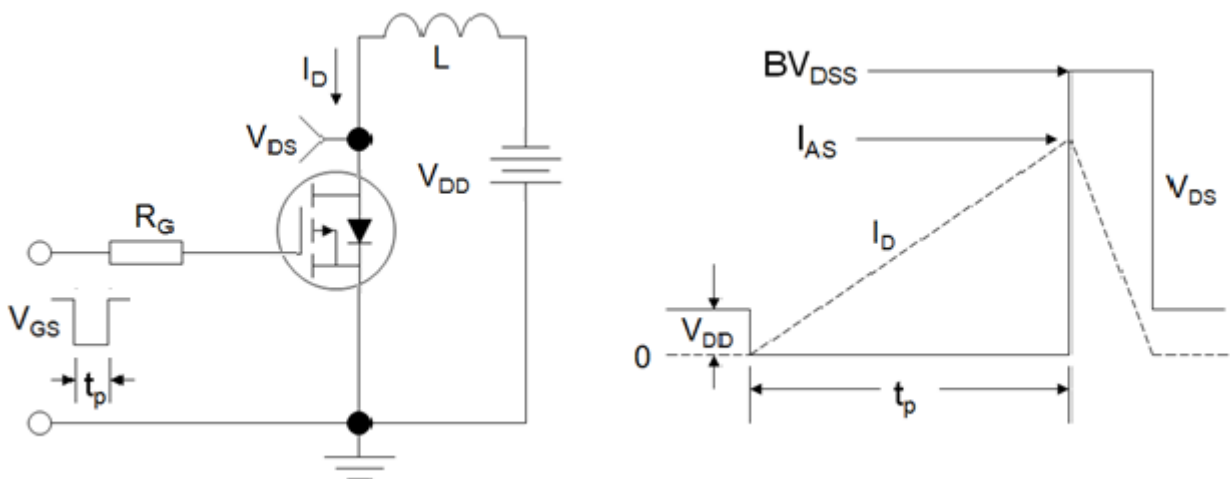
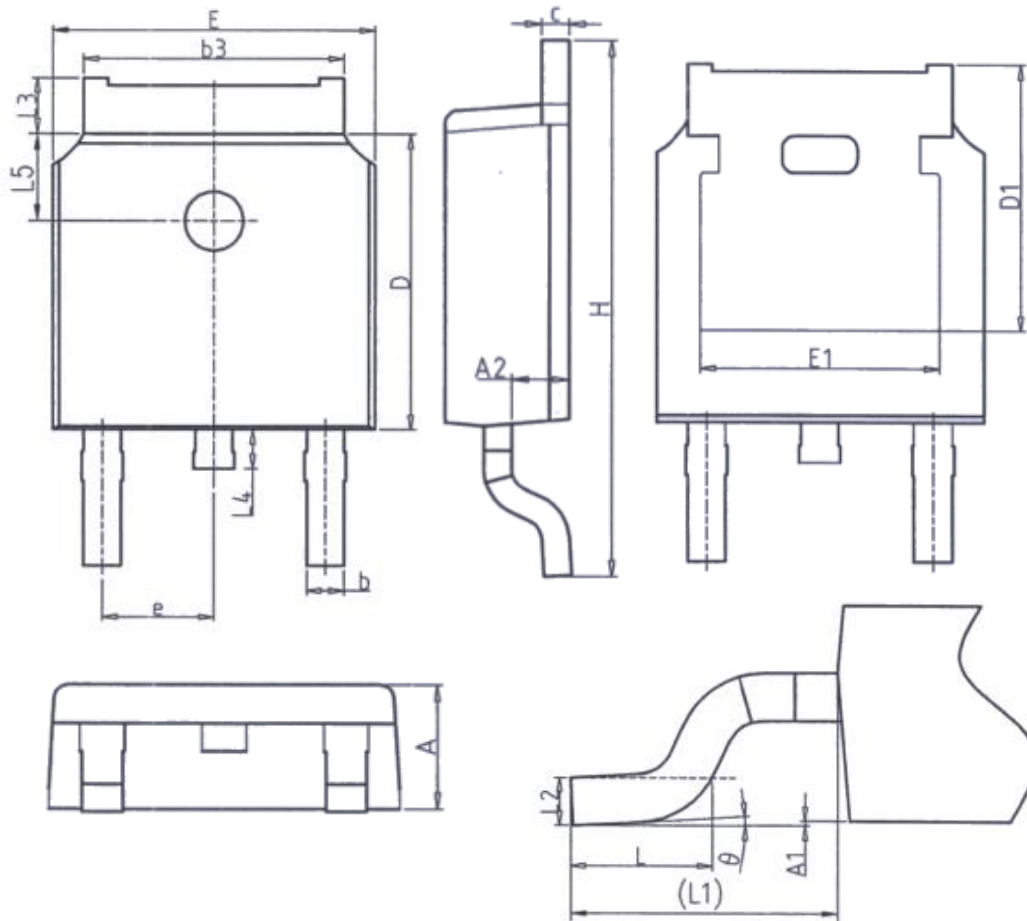


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-252(华天)



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	-

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	-	1.00
L5	1.65	1.95
theta	0°	8°



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